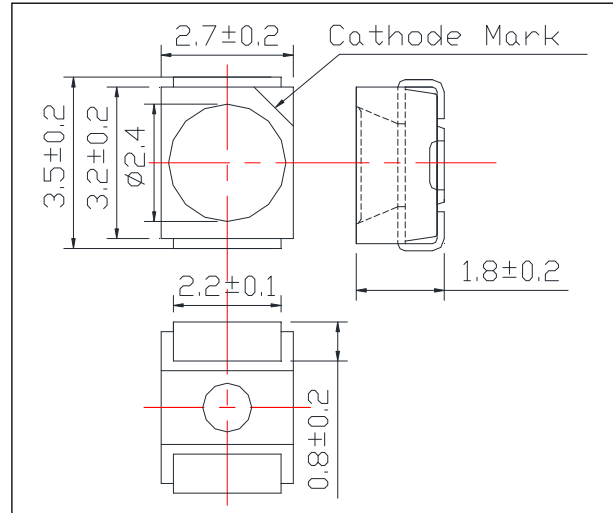


**PD1450T-SMT**  
InGaAs Photodiode

<Specifications>

- Chip Material: InGaAs
- Chip Dimension: 380um x 380um
- Number of Chips: 1pcs
- Lead Frame Die: Silver Plated on Copper
- Package Resin: PA6T
- Lens: Silicone or Epoxy Resin

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Tc=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	VR	20	V
Operating Temperature	TOPR	-40 ~ + 100	°C
Storage Temperature	TSTG	-40 ~+100	°C
Soldering Temperature*	TSOL	250	°C

\* Soldering condition must be completed within 5 seconds at 250°C

Electro-Optical Characteristics [Tc=25°C typ.]						
Item	Symbol	Condition	Min	Typical	Maximum	Unit
Photo Responsivity	RE	VR=5V, λP=1300nm		0.95		A/W
		VR=5V, λP=1550nm		1.00		
Photo Current	IL	VR=0V, λP=1450nm		10		uA
Dark Current	ID	VR=5V			1	nA
Spectral Responsivity(Peak)	λP	VR=0V		1450		nm
Half Angle of Sensitivity	θ1/2	VR=0V		±58		deg
Total Capacitance	CT	VR=5V, f=1MHz		4.5		pF

- Measured by UOS calibrated tool



**Disclaimer**

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.